QFP44-P-1010-0.80B

TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

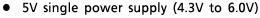
TA8508AF

R/W IC FOR FLOPPY DISK DRIVE

TA8508AF is a bipolar monolithic IC developed as a read/write IC for perpendicular floppy disk drives (PFD). TA8508AF consists of a floppy disk drive read circuit, a write circuit, and various control circuits, all integrated on a single chip to reduce disk drive size and power consumption.

FEATURES

- Power save function which reduces power dissipation (to 9mW typ.) during non-operation (not reading, writing, or erasing).
 - erasing). Weight: : 0.56g (Typ.)



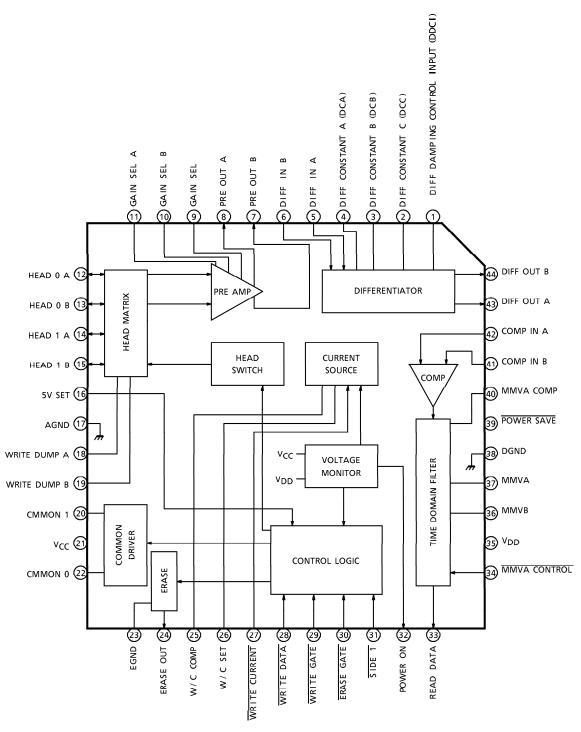
- Incorporates a diode switch for switching between read and write heads. The differential voltage gain of the read amp can be set to 200 times or 400 times using the gain select pin.
- The write current can be set to a maximum of 25mA_{DC} using external resistance.
- A built-in write current switching circuit allows the current value to be switched between outer and inner tracks.
- Read, write, and erase circuits are incorporated in a single chip and can be controlled independently by WG and EG signals.
- A built-in power monitor circuit prevents writing in error at such times as when the power is turned on or abnormal voltage is applied.
- Incorporates a time constant capacitor for the time domain filter. Time constants can be set using an external resistor.
- Incorporates a time constant switching circuit for the time domain filter. Time constants can be switched between outer and inner tracks.
- Incorporates a differentiator constant switching circuit. The differentiator frequency characteristics can be switched.

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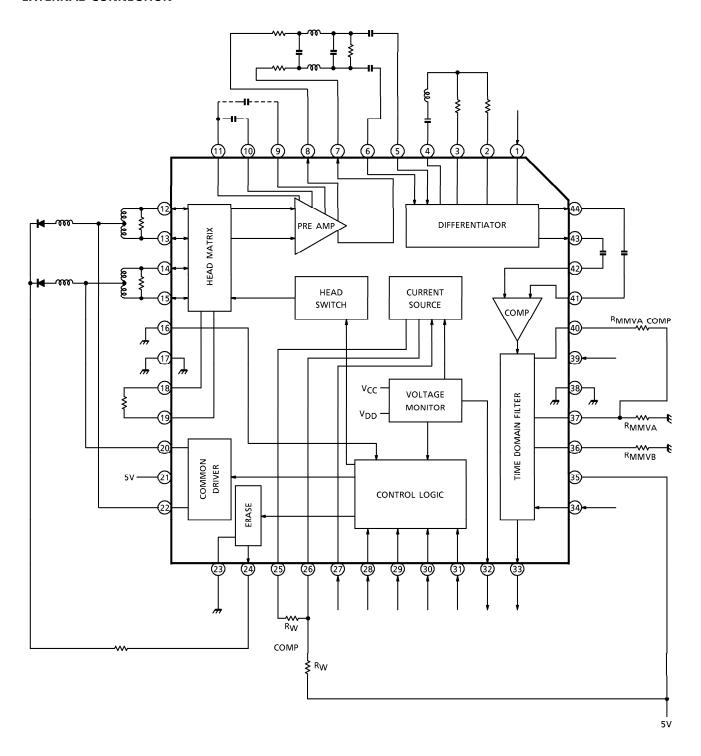
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PIN LAYOUT DIAGRAM/INTERNAL EQUIVALENT BLOCK DIAGRAM



Take care when using pins 9, 11, 12, 13, 14, and 15, as the allowable overvoltage surge margin is small (up to $\pm 100V$).

EXTERNAL CONNECTION



PIN FUNCTION

PIN No.	PIN NAME	PIN FUNCTION
1	DIFF DUMPING CONTROL INPUT	Differentiator constant select pin Inputting low logic voltage selects pins 3 (DCB) and 4 (DCA); inputting high logic voltage selects pins 2 (DCC) and 4 (DCA).
2	DIFF CONSTANT C	Differentiator constant connecting pins
3	DIFF CONSTANT B	These pins connect the differentiator constants between pins 4
4	DIFF CONSTANT A	(DCA) and 2 (DCC), and between pins 4 (DCA) and 3 (DCB).
5	DIFF IN A	Differentiator input pins. These pins input a read signal from the pre-amp output pin to the
6	DIFF IN B	differentiator via the filter circuit.
7	PRE OUT B	Pre-amp output pins These differential output pins output a read signal to the
8	PRE OUT A	differentiator input pin via the filter circuit.
9	GAIN SEL	Pre-amp gain select pins
10	GAIN SEL B	AC coupling of pins 9 and 11 selects a 400-times pre-amp gain. AC
11	GAIN SEL A	coupling of pins 10 and 11 selects a 200-times pre-amp gain.
12	HEAD 0 A	Magnetic head 0 input/output pins These pins connect the write/read magnetic head with a center tap,
13	HEAD 0 B	and the damping resistor at a read.
14	HEAD 1 A	Magnetic head 1 input/output pins
15	HEAD 1 B	Another pair of input/output pins like those above.
16	5V SET	V _{CC} power select input pin Grounding this pin selects V _{CC} = 5V mode.
17	AGND	Analog GND connecting pin
18	WRITE DUMP A	Write dumping resistor connecting pins
19	WRITE DUMP B	The head dumping resistor is connected between these pins at a write.pin voltage at read and write.
20	COMMON 1	Head 1 common driver connecting pin This pin connects to the center tap of magnetic head 1. It sets the head 1 pin voltage at read and write.
21	Vcc	Analog power connecting pin
22	COMMON 0	Head 0 common driver connecting pin This pin connects to the center tap of magnetic head 0. It sets the head 0 pin voltage at read and write.
23	EGND	Erase GND connecting pin
24	ERASE OUTPUT	Erase current sink pin Open collector pin for the erase current sink.
25	W/C COMP	Connecting pin for write current compensation resistor Between this pin and pin 26, connect a write current compensation resistor RW COMP to set the write current increase (IWC). Equation $I_{WC} = \frac{1.3 - V_{WC}}{R_{W} COMP(\Omega)} \times 10 (A_{DC})$
26	W/C SET	Connecting pin for write current setting resistor Between this pin and pin V _{DD} 35, connect a write current setting resistor R _W to set the write current value. Equation $I_W = \frac{1.3}{R_W(\Omega)} \times 10 (A_{DC})$

PIN No.	PIN NAME	PIN FUNCTION
27	WRITE CURRENT	Write current control pin (digital input) When low logic voltage is input, the write current is defined as the sum of IW and IWC. When high logic voltage is input, the write current is IW only.
28	WRITE DATA	Write data input pin (Schmitt digital input) The write data input pin is triggered when digital input goes from high to low.
29	WRITE GATE	Write gate signal input pin (digital input) Inputting low logic voltage activates the write.
30	ERASE GATE	Erase gate signal input pin (digital input) Inputting low logic voltage activates the erase.
31	SIDE 1	Head side switching signal input pin (digital input) Inputting low logic voltage activates head 1; inputting high logic voltage activates head 0.
32	POWER ON	Voltage drop detection output pin This open collector pin outputs low while at least one/both of the VDD and VCC is/are below the specified value.
33	READ DATA	Read data output pin This pin outputs the read data (totem pole type).
34	MMVA CONTROL	Time domain filter time constant switching signal input pin (digital input) Inputting low logic voltage narrows the output width of the first monostable circuit.
35	V_{DD}	Digital power connecting pin
	MMVB	Second monostable circuit R connecting pin for time domain filter Connect the second monostable circuit time constant setting resistor RMMVB. The following equation determines the second monostable circuit's pulse width t_2 . $t_2 = 27 \times (R_{MMVB}(k\Omega) + 0.1)$ (ns)
	MMVA	First monostable circuit R connecting pin for time domain filter. Connect the first monostable circuit time constant setting resistor RMMVA. The following equation determines the first monostable circuit's pulse width t_1 . $t_1 = 53.5 \times (R_A (k\Omega) + 0.1)$ (ns) Note: When MMVA CONTROL logic input voltage is high, $R_A = R_{MMVA}$. When MMVA CONTROL logic input voltage is high, $R_A = R_{MMVA} / R_{MMVA} / R_{MMVA} / R_{MMVA} = R_{MMVA} / R_{MMVA} / R_{MMVA} + R_{MMVA} + R_{MMVA} / R_{MMVA} + R_{MMVA}$
38	DGND	Digital GND connecting pin
39	POWER SAVE	Power save mode select signal input pin (digital input) Inputting low logic voltage selects power save mode, which reduces R/W I _C power dissipation. During power save mode, read, write, and erase operations are disabled. (The power monitor circuit still functions.)
40	MMVA COMP	Resistor connecting pin for time domain filter time constant switching. This open collector pin connects resistor R _{MMVA} COMP between this and pin 37 to compensate the output width of the time domain filter's first monostable circuit.
41	COMP IN B	Comparator input pins
42	COMP IN A	A read signal is input to these two pins from the differentiator output pins via the AC coupling capacitors.
43	DIFF OUT A	Differentiator output pins These two pins output a read signal to the comparator input pin via
44	DIFF OUT B	the AC coupling capacitors.

MAXIMUM RATINGS (Ta = 25° C)

CHARACTERISTICS	SYMBOL	RATING	UNIT
Power Supply Voltage	Vcc	7	V
Supply Voltage	V_{DD}	7	V
Digital Signal Input Voltage (Note 1)	_	-0.5~5.5	V
Voltage Applied to Power On Pin (Note 2)	_	7	٧
Voltage Applied to Erase Output Pin (Note 3)	_	7	>
Voltage Applied to Head 0/1 A/B Pins (Note 4)	_	7	mA
Common Drive Source Current	^I COM	75	mA
Erase Drive Sink Current	ΙΕ	50	mA
Write Drive Current (Note 2)	ΙW	25	mA _{DC}
Sink Current on Power On Pin	_	7	mA
Ambient Operating Temperature	Та	- 20~75	°C
Junction Operating Temperature	Тј	150	°C
Storage Temperature	T _{stg}	- 55∼150	°C
Power Dissipation (Ta = 25°C for IC only) (Note 5)	PD	0.75	W

- (Note1) The WRITE CURRENT, WRITE DATA, WRITE GATE, ERASE GATE, SIDE1, MMVA CONTROL, POWER SAVE, DDCI signals are input to the 5V SET pin.
- (Note2) Applies to POWER ON pin (pin 32).
- (Note3) Applies to ERASE OUTPUT pin (pin 24).
- (Note4) Applies to HEAD 0 A, HEAD 0 B, HEAD 1 A, and HEAD 1 B pins (pins 12, 13, 14, and 15).
- (Note5) For device usage conditions, see Figure 1 Power Dissipation (P_D)-Ambient Temperature (Ta).

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTICS	CONDITIONS	UNIT
V _{CC} , V _{DD} supply voltage	4.3~6.0	V
Operating ambient	0~60	°C
temperature	0~60	

ELECTRICAL CHARACTERISTICS

(1) CURRENT DISSIPATION (Ta = 25°C, $V_{CC} = 5V$, $V_{DD} = 5V$)

CHARACTERISTICS		SYMBOL	TEST CIR- CUIT	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
In Read	V _{DD} Current Dissipation	I _{DDR}	1	_	_	17.7	23.4	mA
III Kead	V _{CC} Current Dissipation	ICCR	1	_	_	7.5	8.6	mA
In Write	V _{DD} Current Dissipation	lDDW	1	(Note 1)	_	9.5	15.4	mA
in write	V _{CC} Current Dissipation		1	_	_	12.3	18.8	mA
In Erase	V _{DD} Current Dissipation	IDDE	1	_	_	9.4	13.9	mA
liii Erase	V _{CC} Current Dissipation	ICCE	1		_	12.6	19.2	mA
In write	V _{DD} Current Dissipation	IDDW + E	1	(Note 1)	_	12.3	19.4	mA
+ Erase	V _C Current Dissipation	ICCW + E	1	<u> </u>	_	12.3	18.8	mA
In Power	V _{DD} Current Dissipation	IDDPS	1	_	_	1.35	2.7	mA
In Power Save	V _{CC} Current Dissipation	ICCPS	1	_	_	0.27	0.4	mA
Jave	Total Power Dissipation	P _{DPS}	1		_	8.1	15.5	mW

(Note 1) When Write Current $I_W = 0$

(2) POWER MONITOR (Ta = 25°C, $V_{CC} = 0 \sim 7V$, $V_{DD} = 0 \sim 7V$)

CHARACTERISTICS		SYMBOL	TEST CIR- CUIT	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{DD} , V _{CC} Threshold	Positive Direction	V _T +	_		_	4.0	4.2	V
Voltage	Negative Direction	V _T -	_	_	3.6	4.0	_	v
Threshold	Voltage Width	V _T + – V _T -	_	_	_	150	_	mV
Power On	Saturation Voltage When Power On Pin (Pin 32) Detection On		_	V _{DD} = 3.6V I _{SINK} = 5mA	_	_	0.4	V
	urrent When PoweR n 32) Detection Off	_		V _{DD} >4.5V	_	_	10	μΑ

(3) PRE-AMP, DIFFERENTIATOR, COMPARATOR (Ta = 25°C, V_{CC} = 5V, V_{DD} = 5V)

	CHARACTERISTICS	SYMBOL	TEST CIR- CUIT	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Differential Voltage	G _{V1}	2	Test Frequency f = 1MHz	340	375	415	V/V
_ ا	Gain	G _{V2}	2	Test Frequency f = 1MHz	170	185	200	L , ,
re-am	Gain Attenuation Bandwidth (– 3dB)	FC	2	_	8	12	_	MHz
ler/Pi	COMMON MODE Rejection Ratio	CMRR	_	Input Sine Wave f=1MHz 200mV _{rms}	50	_	_	dB
Switcher/Pre-amp	Power Supply Rejection Ratio	RSRR	_	Multiplexed sine wave $f = 10kHz \ 1V_{p-p}$	70	_	_	dB
Head	Differential Input Resistance	R _{IN}	_	f = 62.5~625kHz	6.0	9.0	16.0	kΩ
	Differential Input Capacitance	C _{IN}	_	f = 250kHz	_	24	_	рF
	Differential Input Voltage Amplitude	V _{IN}	_	At×200 Gain	0.8	_	7.5	mV _{p-p}
۵	Differential Output Voltage Amplitude	V _{OUT}	2		2.0	3.0	_	V _{p-p}
Pre-Amp	Differential Output Current Amplitude	lout	_		3.0	4.0	5.0	mA _{p-p}
۵.	Differential Output Offset Voltage	V _{OFS}	_	_	_	_	0.5	V
	Input Equivalent Noise Voltage	E _N	2	Head Connected f = 400Hz to 1MHz	_	4.0	6.0	μ V $_{rms}$
	Gain Attenuation Bandwidth (-3dB)	FCD	_	_	20	_	_	MHz
_	Differential Output Voltage Amplitude	V _{OUTD}	_	_	l	2	_	V _{p-p}
Differentiator	Differential Output Offset Voltage	V _{OFD}	_		l	20	_	mV
iffere	Differential Input Resistance	R _{IND}	_	_	16	24	_	kΩ
	Differential Output Resistance	ROUTD	_	_	_	200	_	Ω
	Sink Current (Pins 2, 3, 4)	^I SINKD		_	1.4	2.0	_	mA
Comparator	Maximum Differential Input Voltage Amplitude	VINC	_	_	_	2	_	V _{p-p}
Com	Differential Input Resistance	R _{INC}	_	_	20	32	_	kΩ

(4) TIME DOMAIN/WAVEFORM SHAPING BLOCK (Ta = 25°C, V_{CC} = 5V, V_{DD} = 5V)

	CHARACTERISTICS	SYMBOL	TEST CIR- CUIT	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
First Widtl	Monostable Output Pulse	t ₁	3	_	200	_	3000	ns
	nd Monostable Output Width	t ₂	3	_	100	_	1200	ns
Satur COM	ation Voltage On MMVA P Pin	VMMC	_	ISINK = 10 µA	1	_	50	mV
	Monostable Output Pulse n Precision	E _{TM1}	3	_	- 18	_	18	%
	nd Monostable Output Width Precision	E _{TM2}	3	_	- 20	_	20	%
	Monostable Output Pulse n Compensation Precision	ETM1C	3	_	- 15	_	15	%
Peak	Shift	PS	3	COMP Input f = 62.5 to 500kHz Differential Input = 200mVp-p	_	_	1	%
	Low Output Voltage	V _{LOUT}		I _{OL} = 2mA	_	_	0.5	V
±	High Output Voltage	V _{HOUT}		I _{OH} = -10μA	3.5	_	_	V
Output				I _{OH} = -0.4mA	2.8			
lõ	Sink Current	ISI RD		V _{OUT} = 0.8V	2	4	<u> </u>	mA
	Source Current	Iso RD	<u> </u>	V _{OUT} = 2.8V	0.4	1	_	mA
Read	Rising Time	t _r	3	At Read Output = 0.5 to 2.2V With Load	_	_	25	ns
	Falling Time	tf	3	Capacitance Of 20pF	_	_	25	ns

(5) WRITE SYSTEM/ERASE SYSTEM (Ta = 25° C, $V_{CC} = 5V$, $V_{DD} = 5V$)

	CHARACTERISTICS	SYMBOL	TEST CIR- CUIT	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Output voltage in write selected	Vwсмн	_	$I_W = 25 \text{mA}_{DC}$	4.4	_	_	V
Common Driver	Output voltage in write not-selected	VWCML	_	_	_	_	0.2	V
nomu	Output voltage in read selected	V _{RCMH}	_	_	2.3	2.6	2.9	V
Con	Output voltage in read not-selected	VRCMH	_	_	_	_	0.2	V
	Output current range	Ісом	_	_	—	—	75	mA
river	ERASE OUTPUT pin output saturation voltage	V _{ER}	_	I _{Erase} = 50mA	_	0.2	0.5	V
Erase Driver	ERASE OUTPUT pin leakage current	ILKER	_	_	_	_	15	μΑ
□	Erase current range	^I ERASE	_	_	_	_	50	mA
	Write current setting	EW			-8	_	8	%
1	precision	EWC		_	- 10	_	10	70
er	Write current output imbalance	DW	_	_	-	_	1	%
Write Driver	Write current variable range (one side)	lw		— V _{DD} = 5.0V, Ta = 25°C	<u>-</u>	_	20 28	mA _{DC}
Write	Write current compensation variable range (one side)	lwc	_	_	_	_	5	mA _{DC}
	W/C COMP pin saturation voltage	Vwc	_	I _{source} = 0.5mA	_	50	300	mV
in Write B Pins	Leakage Current	ILKW	_	_	_	_	10	μΑ
4·15) in	Saturation voltage	V _{SAT}	_	_	_	2	_	V
(Pins 12·13·14·15) HEAD 0/1 A/I	Differential output capacitance	COUT		_	_	23	_	pF
(Pins HE	Differential output resistance	ROUT	_	f = 1MHz	_	280	_	kΩ

(6) LOGIC INPUT/OUTPUT BLOCK (Ta = 25° C, $V_{CC} = 5V$, $V_{DD} = 5V$)

	CHARACTERIST	TICS	SYMBOL	TEST CIR- CUIT	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Low Logic Inpu	t Voltage	V_{LIN}	_	_	—	_	0.8	V
İ	High Logic Inpu	ut Voltage	VHIN	_	_	2.0	_	_	V
Input	Low Logic Input Current	PS Pin (Pin 39)	I _{LIN}	_	0.4V Applied	_	-	50	μΑ
la l	Imput Current	Others		_	0.4V Applied	—	_	250	
Digital Signal Input	High Logic Inpu (Pins 28, 29, 30		I _{HIN1}	_	2.4V Applied	_	_	10	μΑ
Digita	High Logic Inpu (Pin 27)	ut Current	lHIN2	_	2.4V Applied	_	_	130	μ A
	High Logic Input Current (Pin 34)		I _{HIN3}		2.4V Applied	_	ı	80	μΑ
Digital Input	Negative Direct Threshold Volta (Input H → L)		V _{LINS}		_	0.8	1.0		V
Schmitt Di Signal In	Positive Direction Threshold Volta (Input L → H)		V _{HINS}	_	_	_	1.6	2.0	V
S	Hysteresis Volta	ge Width	V _{HINS} - V _{LINS}	_	_	0.3	0.6	_	V
Write Data	Write Data Max Input Frequency		fIND	_	V _{IN} = 0.8~2.2V (50% Duty)	_	_	12	MHz

(7) SWITCHING CHARACTERISTICS (Ta = 25°C, V_{CC} = 5V, V_{DD} = 5V)

CHARACTERISTICS	SYMBOL	TEST CIR- CUIT	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Recovery Time From Power Save to Read Mode	_	_	PS off→DIFF Output 90 to 110% (Note 1)	_	1	2	ms
Head Switching Time	_	_	SIDE1 50%→Selected V _{COM} 90%, Head Pin and Common Pin Connected	_	_	4	μs
Read to write mode	_	—	WG Off→Selected V _{COM} 90%	_	_	1	μ s
WD-lw Delay	_	_	WD 50%→I _W 50%	_	_	0.3	μs
Write Current Rise Time	_	_	L _h = 0mH	_	_	0.1	μs
Recovery Time From Erase Mode to Read Mode	_	_	EG Off→ DIFF Output 90 to 110%	_	_	20	μs
Read Recovery Time	_	_	WG, EG Off→ DIFF Output 90%	_	30	40	μs
Sink Current Rise and Fall Time When Power Monitor Detection Turned Off or Off	_	_	Load (Pin 32) ₹ □ □ □ □ □ □ □ □ □ □ □ □ □ □ □ □ □ □	_	_	100	ms

Note 1: When returning from power save to read mode, raise $\overline{\text{WG}}$ and $\overline{\text{EG}}$ to high level $10\,\mu\text{s}$ before $\overline{\text{PS}}$ goes from low to high.

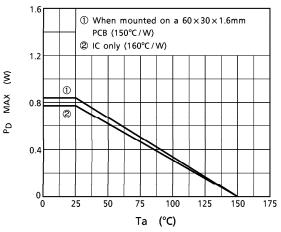
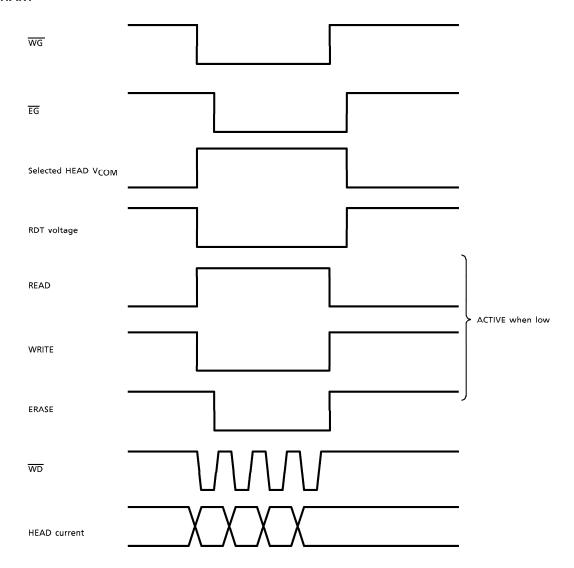


Fig.1 Power dissipation (PD) – Ambient Temperature (Ta)

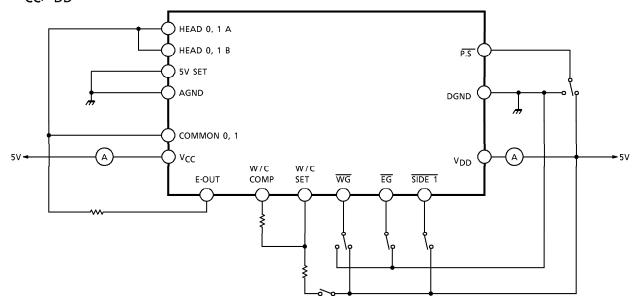
The TA8508AF maximum operating ambient temperature (Ta) is 75° C. However, refer to the above graph when using, as the package's power dissipation (PD) varies according to the ambient temperature.

TIMING CHART

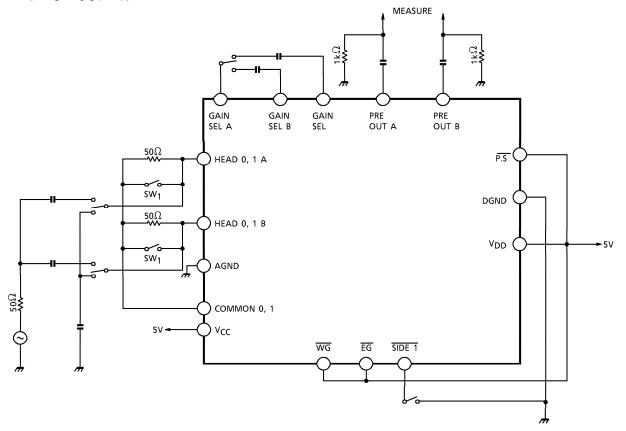


TEST CIRCUIT

1. Icc, IDD



2. G_V, F_C, V_{OUT}, E_N

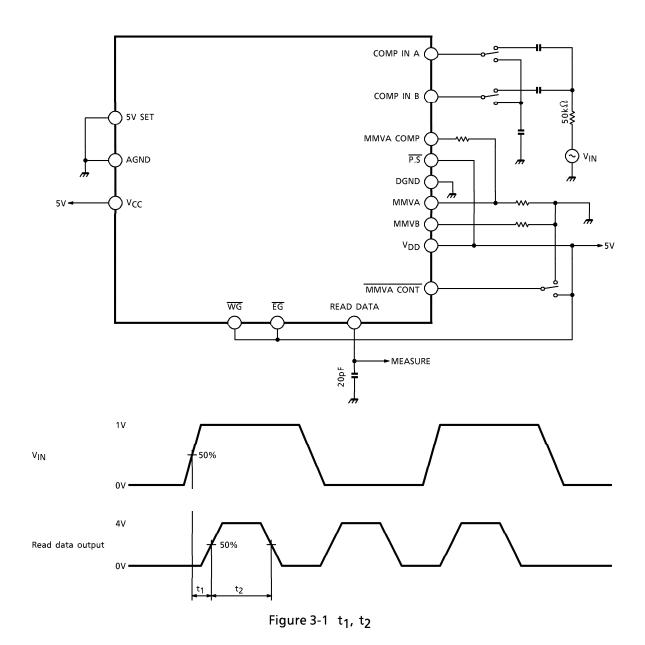


Note1: When G_V, F_C, or V_{OUT} is measured, the signal is input to either of the HEAD 0, 1

A pins or HEAD 0, 1 B pins, whichever pair is selected.

Note2: Turn SW_1 off only when measuring E_N .

3. t₁, t₂, ETM1, ETM2, ETM1C, PS, t_r, t_f



(1) First and second monostable output pulse precision

Connect R_{MMVA} to set t_1 to 1μ s and connect R_{MMVB} to set t_2 to 0.5μ s. Observe t_1 and t_2 in the read data output.

ETM1 and ETM2 are defined as: ETM1 =
$$(1 - t_1 / 1) \times 100 (\%)$$

STM2 = $(1 - t_2 / 0.5) \times 100 (\%) (t_1 (μ s), t_2 (μ s))$

(2) First monostable output pulse width compensation precision

Connect R_{MMVA}, R_{MMVA} COMP so that t_1 to t'_1 (the difference between t_1 prior to pulse width compensation and t'_1 after pulse width compensation) is 1μ s.

Observe t'₁ and t₁ when 0.8V and 2.0V are applied to MMVA CONTROL.

EMT1C is defined as:

EMT1C =
$$(1 - (t_1 - t'_1)/1) \times 100 (\%) (t_1 (\mu s), t'_1 (\mu s))$$

(3) Peak shift

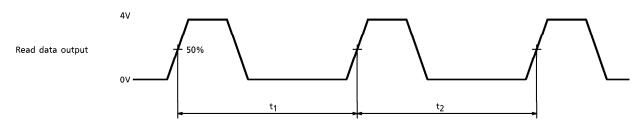


Figure 3.2 P.S.

$$PS = \frac{1}{2} \times \left| \frac{t_1 - t_2}{t_1 + t_2} \right| \times 100 \, (\%)$$

(4) Read data output rise and fall times

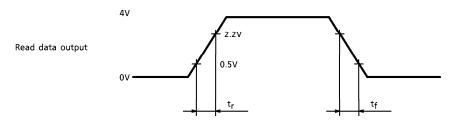
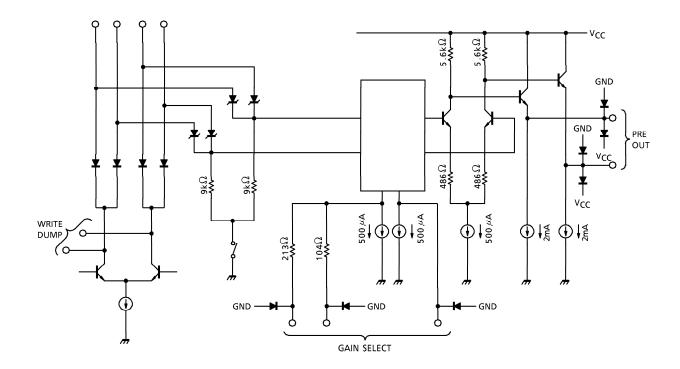


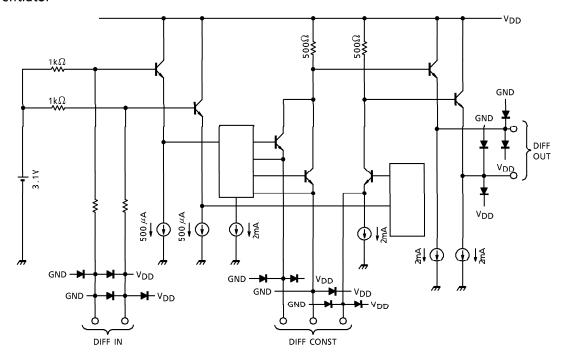
Figure 3.3 t_r and t_f

INTERNAL EQUIVALENT CIRCUITS

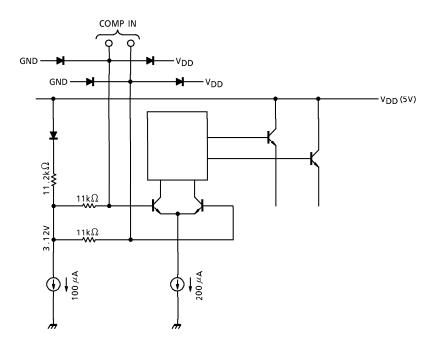
1. Pre-amp



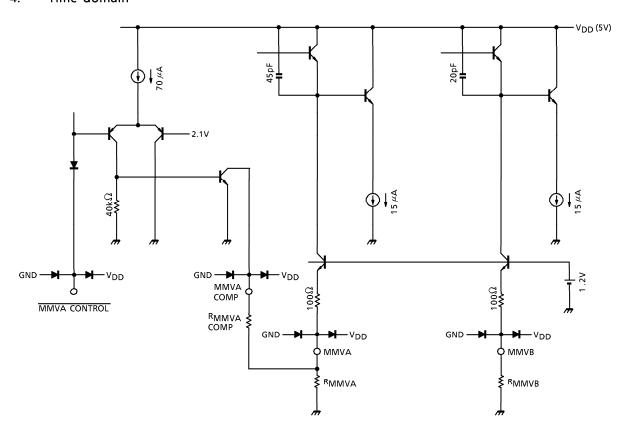
2. Differentiator



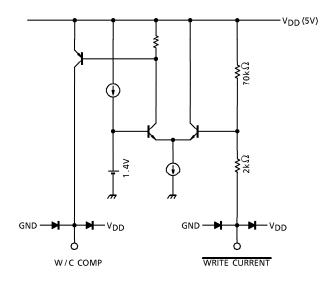
3. Comparator



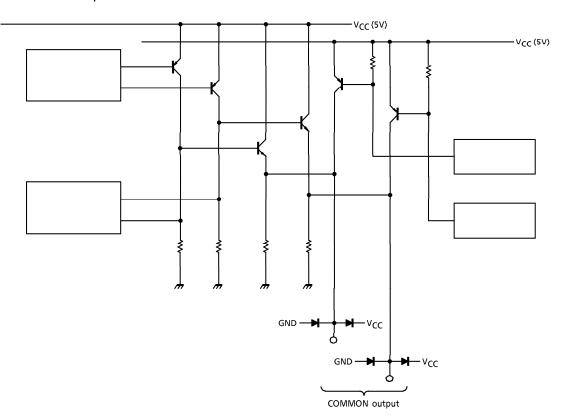
4. Time domain



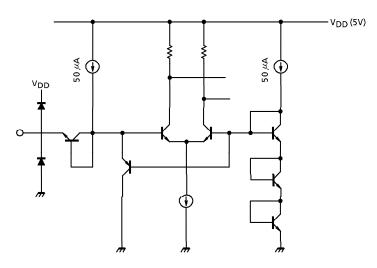
5. W/C control



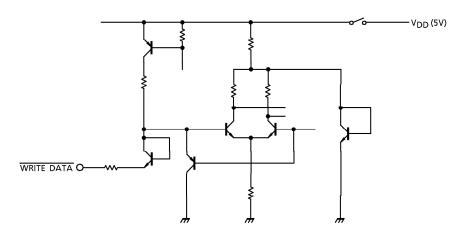
6. Common driver output



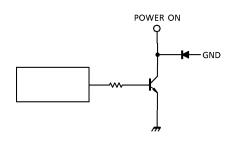
7. WRITE GATE, ERASE GATE, SIDE1 interface pins



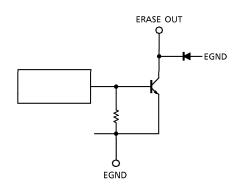
8. WRITE DATA interface pin



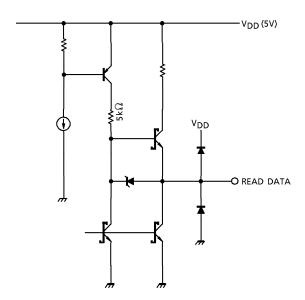
9. Power monitor output



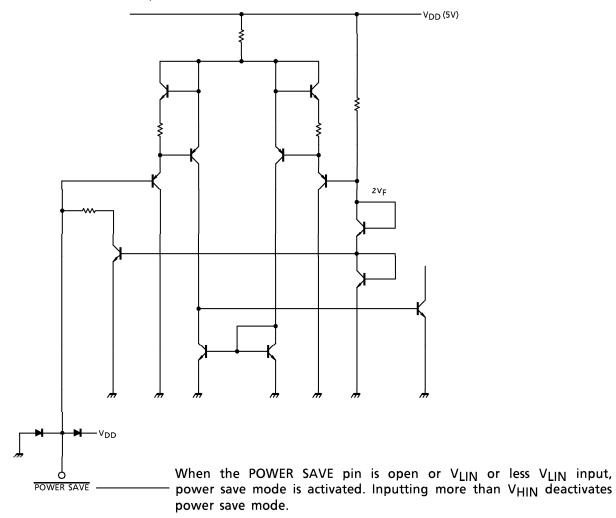
10. Erase output



11. Read data output



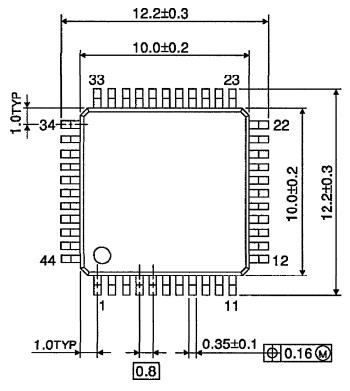
12. POWER SAVE interface pin

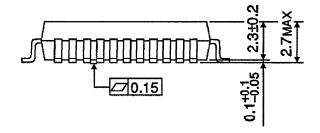


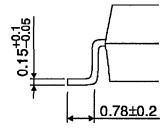
OUTLINE DRAWING

QFP44-P-1010-0.80B

Unit: mm







Weight: 0.56g (Typ.)